

Supplementary Material:

Two-dimensional Janus α -Au₂XY ($X, Y = \text{S/Se/Te}$) semiconductors with favourable band-gap and high carrier mobility by first-principles investigations

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Table S1. Atomic positions of Janus α -Au₂XY ($X/Y = \text{S, Se, Te}$).

		x	y	z
Janus α -Au ₂ SSe	Au1	0.5	0.507408166449272	0.358390690580377
	Au2	0.0	0.99322295285337	0.357643929463856
	S	0.5	0.82620184992071	0.296451043606626
	Se	0.5	0.174167067776642	0.424514372349141
Janus α -Au ₂ STe	Au1	0.5	0.518227356133014	0.358340755443204
	Au2	0.0	0.982610295119442	0.355595155112203
	S	0.5	0.826650727226904	0.291043796096068
	Te	0.5	0.173511658520631	0.432020329348523
Janus α -Au ₂ SeTe	Au1	0.5	0.511598232065798	0.359339053898884
	Au2	0.0	0.989195404514621	0.357223150877916
	Se	0.5	0.829519690693376	0.284646317122251
	Te	0.5	0.1706867097262	0.435791514100957

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